

#### Replaces DS5481-1.4

# DFM1200EXM12-A000

## Fast Recovery Diode Module

DS5481-2 August 2011 (LN28650)

### **FEATURES**

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Volt Drop
- Isolated AISiC Base with AIN Substrates
- Triple Diodes can be paralleled for 3600A rating
- Lead Free Construction

### **APPLICATIONS**

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuits
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM1200EXM12-A000 is a triple 1200V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

### **ORDERING INFORMATION**

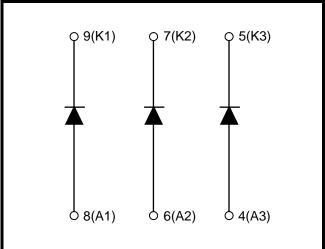
Order As:

### DFM1200EXM12-A000

Note: When ordering, please use the complete part number

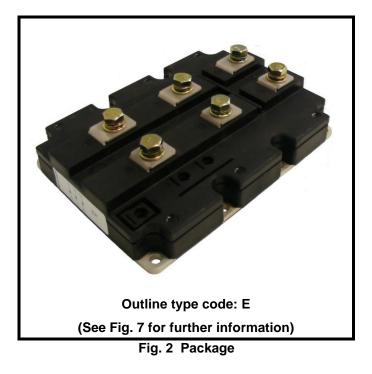
## **KEY PARAMETERS**

V <sub>RRM</sub>		1200V
VF	(typ)	1.9V
I <sub>F</sub>	(max)	1200A
I <sub>FM</sub>	(max)	2400A



External connection required for a single 3600A diode

Fig. 1 Circuit configuration



## ABSOLUTE MAXIMUM RATINGS - PER ARM

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

#### T<sub>case</sub> = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>RRM</sub>	Repetitive peak reverse voltage	T <sub>j</sub> = 125°C	1200	V
I <sub>F</sub>	Forward current	DC, $T_{case} = 75^{\circ}C$ , $T_{j} = 125^{\circ}C$	1200	А
I <sub>FM</sub>	Max. forward current	$T_{case} = 110^{\circ}C, t_{p} = 1ms$	2400	А
l <sup>2</sup> t	I <sup>2</sup> t value fuse current rating	$V_{R} = 0, t_{p} = 10ms, T_{j} = 125^{\circ}C$	400	kA <sup>2</sup> s
P <sub>max</sub>	Max. transistor power dissipation	$T_{case} = 25^{\circ}C, T_{j} = 125^{\circ}C$	7520	W
V <sub>isol</sub>	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V
QPD	Partial discharge – per module	IEC1287, V1 = 1300V, V2 = 1000V, 50Hz RMS	10	рС

## THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AIN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
R <sub>th(j-c)</sub>	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	20	°C/kW
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	°C/kW
Tj	Junction temperature		-	-	125	°C
T <sub>stg</sub>	Storage temperature range		-40	-	125	°C
	Corow Torque	Mounting – M6	-	-	5	Nm
Screw Torque		Electrical connections – M8	-	-	10	Nm

## STATIC ELECTRICAL CHARACTERISTICS – PER ARM

#### T<sub>case</sub> = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I <sub>RM</sub>	Peak reverse current	V <sub>R</sub> = 1200V, T <sub>j</sub> = 125°C			30	mA
V <sub>F</sub>	Forward voltage	I <sub>F</sub> = 1200A		1.9	2.2	V
		I <sub>F</sub> = 1200A, T <sub>j</sub> = 125°C		2.1	2.4	V
L <sub>M</sub>	Inductance			20		nH

## STATIC ELECTRICAL CHARACTERISTICS

#### T<sub>case</sub> = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
L <sub>M</sub>	Module inductance (externally connected in parallel)			15		nH

## **DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM**

#### T<sub>case</sub> = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q <sub>rr</sub>	Reverse recovery charge	I <sub>F</sub> = 1200A		200		μC
I <sub>rr</sub>	Peak reverse recovery current	$V_R = 600V$		800		А
E <sub>rec</sub>	Reverse recovery energy	dI <sub>F</sub> /dt = 9000A/µs		80		mJ

### T<sub>case</sub> = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q <sub>rr</sub>	Reverse recovery charge	I <sub>F</sub> = 1200A		300		μC
l <sub>rr</sub>	Peak reverse recovery current	$V_R = 600V$		920		А
E <sub>rec</sub>	Reverse recovery energy	dI <sub>F</sub> /dt = 8400A/µs		140		mJ

3200 100 25 °C Transient thermal impedance, Z<sub>th(j-c)</sub> - (°C/kW) 125 °C 2800 2400 Forward current, Ir - (A) 2000 10 1600 1200 800 400 R<sub>i</sub> (°C/kW) 0.80 2.74 3.49 13.0 τ<sub>i</sub> (ms) 0.01 1.43 12.8 110 0 1 0 0.5 1 1.5 2 2.5 3 3.5 0.001 0.01 0.1 1 10 Forward voltage, V<sub>f</sub> - (V) Pulse width, tp - (s) Fig. 3 Diode typical forward characteristics Fig. 4 Transient thermal impedance 2200 1400 2000 1200 1800 Reverse recovery current, I<sub>rr</sub> - (A) 1600 1000 1400 800 1200 1000 600

400

200

0

0

200

400

600

Reverse Voltage, V<sub>R</sub> - (V)

Fig. 6 RBSOA

800

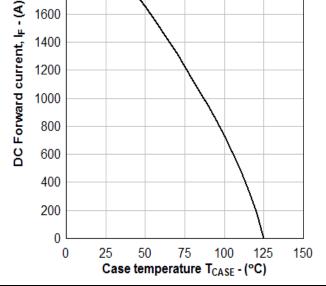


Fig. 5 DC Current rating vs case temperature

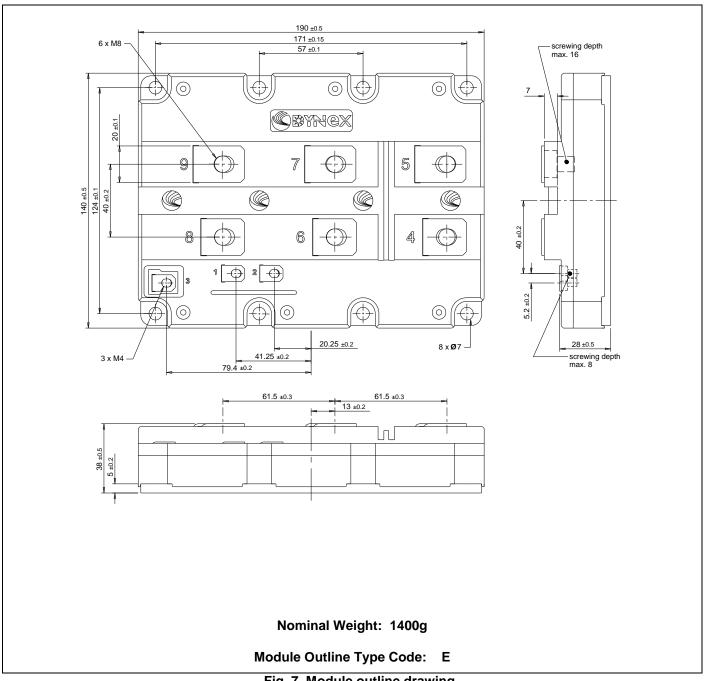
1000 1200

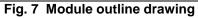
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For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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